

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	134	((wash\$4 or rins\$5) and (pure adj water) and (nozzle) and ((semiconductor or silicon or ("Si"))) adj substrate) and ((high adj molecular) or polymer or monomer)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:14
L2	58	1 and spray	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:14
L3	78	1 and spray\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:15
L4	25	(wash\$4 or rins\$5) and ((semiconductor or silicon or ("Si"))) adj substrate) and (((behenic adj acid) or ("C.sub.27 H.sub.46 O")) or ((cholesterin) or ("C.sub.21 H.sub.43 COOH")))) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:18
L5	33	((wash\$5 or clean\$5) adj ((semiconductor or silicon or ("Si"))) adj substrate)) and (organic or polymer or monomer) and (boil\$4 adj point)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:22
L6	10	((wash\$5 or clean\$5) adj ((semiconductor or silicon or ("Si"))) adj substrate)) and (organic or polymer or monomer) and (boil\$4 adj point) and ((temperature or heat) adj treat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:22
L7	29	((wash\$5 or clean\$5) adj ((semiconductor or silicon or ("Si"))) adj substrate)) and (organic or polymer or monomer) and (boil\$4 adj point) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:23
L8	8	((wash\$5 or clean\$5) adj ((semiconductor or silicon or ("Si"))) adj substrate)) and (organic or polymer or monomer) and (boil\$4 adj point) and ((temperature or heat) adj treat\$5) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:23

L9	890	(438/758).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 09:49
S1	2	((wash\$4 or rins\$5) with ((semiconductor or silicon or ("Si")) adj substrate) with (high adj molecular)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/05 10:34
S2	16	((wash\$4 or rins\$5) same ((semiconductor or silicon or ("Si")) adj substrate) same (high adj molecular)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/05 10:42
S3	692	(wash\$4 or rins\$5) and ((semiconductor or silicon or ("Si")) adj substrate) and (high adj molecular) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/05 10:42
S4	22	(wash\$4 or rins\$5) and ((semiconductor or silicon or ("Si")) adj substrate) and ((behenic adj acid) or (cholesterin)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 12:52
S5	22	(wash\$4 or rins\$5) and ((semiconductor or silicon or ("Si")) adj substrate) and (((behenic adj acid) or ("C.sub.27 H.sub.46 O")) or ((cholesterin) or ("C.sub.21 H.sub.43 COOH")))) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:18
S6	2	("6165956").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 13:22
S7	5119	(wash\$4 or rins\$5 or clean\$6) and ((behenic adj acid) or (cholesterin)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 12:55
S8	2	((wash\$4 or rins\$5 or clean\$6) near (semiconductor)) and ((behenic adj acid) or (cholesterin)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 12:55

S9	22	((wash\$4 or rins\$5 or clean\$6) with (semiconductor)) and ((behenic adj acid) or (cholesterin)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 12:55
S10	737	((wash\$4 or rins\$5 or clean\$6) and (semiconductor)) and ((behenic adj acid) or (cholesterin)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 12:55
S11	51	((wash\$4 or rins\$5 or clean\$6) same (semiconductor)) and ((behenic adj acid) or (cholesterin)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 13:11
S12	4293	((wash\$4 or rins\$5 or clean\$6) and (semiconductor)) and (high adj molecular) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 13:11
S13	791	((wash\$4 or rins\$5 or clean\$6) same (semiconductor)) and (high adj molecular) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 13:13
S14	451	((wash\$4 or rins\$5 or clean\$6) with (semiconductor)) and (high adj molecular) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 13:13
S15	371	((wash\$4 or rins\$5 or clean\$6) near10 (semiconductor)) and (high adj molecular) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/15 13:13
S16	10	((semiconductor or silicon) adj substrate) same ((organic adj molecule\$1) near3 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/05 14:07
S17	3	((("20030171239") or ("6689473") or ("5970381"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/22 14:05

S18	30	((("4722906") or ("4826759") or ("4973493") or ("4979959") or ("5002582") or ("5073484") or ("5217492") or ("5258041") or ("5263992") or ("5414075") or ("5512329") or ("5512474") or ("5563056") or ("5637460") or ("5654162") or ("5707818") or ("5714360") or ("5741551") or ("5744515") or ("5783502") or ("5858653") or ("5942555") or ("5981298") or ("6007833") or ("6020147") or ("6077698") or ("6090995") or ("6121027") or ("6156345") or ("6214901"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/05 14:22
S19	2	("20020158256").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/30 09:47
S21	2	("20010005601").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/30 12:57
S22	2	("6294406").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/30 12:57
S23	8	((("6762078") or ("6395578") or ("6515356") or ("6501184"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/30 13:12
S29	2	("6294406").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/30 13:30
S30	2	("6531350").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/30 13:30

S32	5	gate and source and drain and (light adj dop\$6) and ((deep or depth) adj dop\$6) and silicide and plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/30 13:38
S35	4	((("5918130") or ("6087235")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/30 13:44
S52	61	gate and source and drain and (light\$3 adj dop\$6) and ((depth or deep or expand\$5) adj dop\$6) and (plug)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/30 14:02
S53	50	gate and source and drain and (light\$3 adj dop\$6) and ((depth or deep or expand\$5) adj dop\$6) and silicide and (plug)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/30 14:31
S77	2	("5427964").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/07 14:15
S83	2	((("5932493") or ("6165956")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/04/06 14:44
S84	802	(438/758).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 09:49
S85	751	(wash\$4 or rins\$5) and ((semiconductor or silicon or ("Si")) adj substrate) and (high adj molecular) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/05 10:42
S87	21	((wash\$4 or rins\$5) with ((semiconductor or silicon or ("Si")) adj substrate) with ((high adj molecular) or polymer or monomer)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/05 10:43

S88	1	((wash\$4 or rins\$5) same (pure adj water) same (nozzle) same ((semiconductor or silicon or ("Si"))) adj substrate) same ((high adj molecular) or polymer or monomer)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/06 13:25
S89	1	((wash\$4 or rins\$5) same ((pure or purif\$6) adj water) same (nozzle) same ((semiconductor or silicon or ("Si"))) adj substrate) same ((high adj molecular) or polymer or monomer)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/06 13:15
S90	155	((wash\$4 or rins\$5) same ((semiconductor or silicon or ("Si"))) adj substrate) same ((high adj molecular) or polymer or monomer)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/06 13:18
S91	1	((wash\$4 or rins\$5) same (water) same (nozzle) same ((semiconductor or silicon or ("Si"))) adj substrate) same ((high adj molecular) or polymer or monomer)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/06 13:25
S92	130	((wash\$4 or rins\$5) and (pure adj water) and (nozzle) and ((semiconductor or silicon or ("Si"))) adj substrate) and ((high adj molecular) or polymer or monomer)) and @ad<="20030912"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:14
S93	54	S92 and spray	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:14
S94	74	S92 and spray\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:15